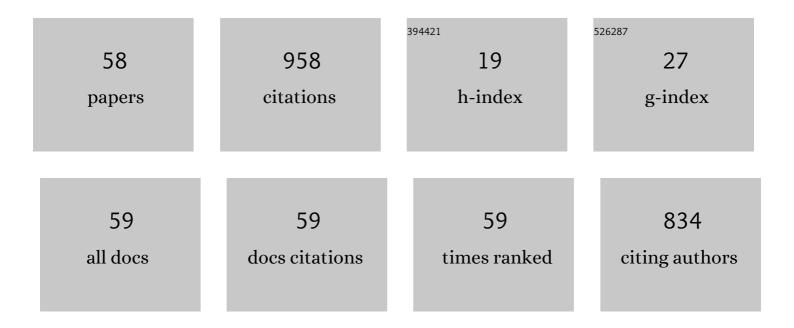
## Murat Soylu

List of Publications by Year in descending order

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#	Article	IF	CITATIONS
1	Photoelectrical characterization of a new generation diode having GaFeO3 interlayer. Solar Energy Materials and Solar Cells, 2014, 124, 180-185.	6.2	54
2	Barrier characteristics of gold Schottky contacts on moderately doped n-InP based on temperature dependent l–V and C–V measurements. Microelectronic Engineering, 2009, 86, 88-95.	2.4	52
3	Analysing space charge-limited conduction in Au/n-InP Schottky diodes. Physica E: Low-Dimensional Systems and Nanostructures, 2010, 43, 534-538.	2.7	52
4	Analysis of barrier height inhomogeneity in Au/n-GaAs Schottky barrier diodes by Tung model. Journal of Alloys and Compounds, 2010, 506, 418-422.	5.5	45
5	Photovoltaic and interface state density properties of the Au/n-GaAs Schottky barrier solar cell. Thin Solid Films, 2011, 519, 1950-1954.	1.8	45
6	Effects of interface states and series resistance on electrical properties of Al/nanostructure CdO/p-GaAs diode. Journal of Alloys and Compounds, 2012, 541, 462-467.	5.5	37
7	Transparent CdO/n-GaN(0001) heterojunction for optoelectronic applications. Journal of Physics and Chemistry of Solids, 2015, 85, 26-33.	4.0	36
8	Ruthenium(II) Complex Based Photodiode for Organic Electronic Applications. Journal of Electronic Materials, 2018, 47, 828-833.	2.2	35
9	Solar light sensitive photodiode produced using a coumarin doped bismuth oxide composite. Materials Science in Semiconductor Processing, 2019, 90, 129-142.	4.0	31
10	Electrical and optical properties of ZnO/Si heterojunctions as a function of the Mg dopant content. Materials Science in Semiconductor Processing, 2015, 29, 76-82.	4.0	27
11	Photodiode Based on CdO Thin Films as Electron Transport Layer. Journal of Electronic Materials, 2016, 45, 5756-5763.	2.2	26
12	Controlling the properties of ZnO thin films by varying precursor concentration. Journal of Alloys and Compounds, 2018, 741, 957-968.	5.5	26
13	Influence of illumination intensity and temperature on the electrical characteristics of an Al/p-GaAs/In structure prepared by thermal evaporation. Microelectronic Engineering, 2012, 99, 50-57.	2.4	25
14	Modification of electrical properties of Al/p-Si Schottky barrier device based on 2′-7′-dichlorofluorescein. Journal of Applied Physics, 2011, 110, .	2.5	24
15	The electrical characterization of ZnO/GaAs heterojunction diode. Physica E: Low-Dimensional Systems and Nanostructures, 2014, 64, 240-245.	2.7	23
16	Optoelectrical properties of Al/p-Si/Fe:N doped ZnO/Al diodes. Thin Solid Films, 2018, 653, 236-248.	1.8	23
17	The effect of thickness of organic layer on electronic properties of Al/Rhodamine B/p-Si structure. Materials Science in Semiconductor Processing, 2011, 14, 212-218.	4.0	22
18	The effects of annealing on Au/pyronine-B/MD n-InP Schottky structure. Journal of Physics and Chemistry of Solids, 2010, 71, 1398-1403.	4.0	21

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19	Controlling of conduction mechanism and electronic parameters of silicon–metal junction by mixed Methylene Blue/2′-7′-dichlorofluorescein. Microelectronics Reliability, 2013, 53, 1901-1906.	1.7	21
20	Effect of calcination and carbon incorporation on NiO nanowires for photodiode performance. Microelectronic Engineering, 2018, 202, 51-59.	2.4	19
21	Analysis of photovoltaic behavior of Si-based junctions containing novel graphene oxide/nickel(II) phthalocyanine composite films. Microelectronic Engineering, 2016, 154, 53-61.	2.4	18
22	Study of optical and electrical assessments of the quaternary MgZnSnO system containing different Mg content. Journal of Materials Science: Materials in Electronics, 2014, 25, 4235-4245.	2.2	17
23	Controlling of electronic parameters of GaAs Schottky diode by poly(3,4-ethylenedioxithiophene)-block-poly(ethylene glycol) organic interlayer. Microelectronic Engineering, 2011, 88, 867-871.	2.4	15
24	On the energy distribution of interface states and their relaxation time profiles in Al/pentacene/p-GaAs heterojunction diode. Journal of Applied Physics, 2012, 111, 034508.	2.5	15
25	Barrier height enhancement and temperature dependence of the electrical characteristics of Al Schottky contacts on p-GaAs with organic Rhodamine B interfacial layer. Superlattices and Microstructures, 2012, 52, 470-483.	3.1	14
26	Composite CuFe 1â^'x Sn x O 2 / p -type silicon photodiodes. Spectrochimica Acta - Part A: Molecular and Biomolecular Spectroscopy, 2017, 180, 110-118.	3.9	14
27	Dye based photodiodes for solar energy applications. Applied Physics A: Materials Science and Processing, 2017, 123, 1.	2.3	14
28	Properties of PEDOT:PEG/ZnO/p-Si heterojunction diode. Materials Science and Engineering B: Solid-State Materials for Advanced Technology, 2012, 177, 785-790.	3.5	13
29	Electrical characteristics of Au/Pyronine-B/moderately doped n-type InP Schottky structures in a wide temperature range. Journal of Alloys and Compounds, 2011, 509, 5105-5111.	5.5	12
30	Rectifying structure with high voltage operation based on CuBO 2 as an UV photocatalyst. Journal of Alloys and Compounds, 2014, 617, 602-608.	5.5	12
31	Analysis of photoconductive mechanisms of organic-on-inorganic photodiodes. Physica E: Low-Dimensional Systems and Nanostructures, 2017, 93, 284-290.	2.7	12
32	Solution molarity dependent structural and optical properties of CdO nanostructured thin films. Optik, 2020, 216, 164865.	2.9	12
33	Properties of sol–gel synthesized n-ZnO/n-GaN (0001) isotype heterojunction. Materials Chemistry and Physics, 2014, 143, 495-502.	4.0	11
34	CdO thin films based on the annealing temperature differences prepared by sol–gel method and their heterojunction devices. Materials Research Express, 2017, 4, 126307.	1.6	11
35	Fabrication and electrical characteristics of Perylene-3,4,9,10-tetracarboxylic dianhydride/p-GaAs diode structure. Microelectronics Reliability, 2012, 52, 1355-1361.	1.7	10
36	Correlations for coumarin additive on the electrical and photocatalytic activity of TiO2 modified by thiourea. Microelectronic Engineering, 2016, 154, 26-37.	2.4	10

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37	The validity of Kohlrausch law for the photocurrent transient and the role of N 2 /Ar flow ratio in photoconductivity of sputtered CoZnO. Journal of Alloys and Compounds, 2017, 712, 152-163.	5.5	10
38	A novel photodiode based on Ruthenium(II) complex containing polydentate pyridine as photocatalyst. Microelectronics Reliability, 2015, 55, 2685-2688.	1.7	9
39	Fabrication and characterization of light-sensing device based on transparent ZnO thin film prepared by sol-gel. Optik, 2016, 127, 8479-8486.	2.9	9
40	Preparation of Tungsten Trioxide Nanorods by Hydrothermal Route: <i>n</i> -Tungsten Trioxide Nanorods/ <i>p</i> -Silicon <i>p</i> – <i>n</i> Junction. Journal of Nanoelectronics and Optoelectronics, 2014, 9, 327-333.	0.5	9
41	A Temperature Sensor Based on Al/p-Si/CuCdO2/Al Diode for Low Temperature Applications. Journal of Electronic Materials, 2020, 49, 2317-2325.	2.2	8
42	ZnO nanostructured thin films: Structural and optical properties controlled by ruthenium content. Superlattices and Microstructures, 2014, 67, 144-155.	3.1	7
43	CdS Quantum Dots and Dye Co-Sensitized Nanorods TiO <sub>2</sub> Solar Cell. Journal of Nanoelectronics and Optoelectronics, 2014, 9, 662-665.	0.5	7
44	Fabrication and characterization of transparent MEH-PPV/n-GaN (0001) heterojunction devices. Optical Materials, 2012, 34, 878-883.	3.6	6
45	Dopant-induced photoresponsivity in coumarin-dye-sensitized nanowire NiO/p-Si heterojunction. Materials Science in Semiconductor Processing, 2020, 106, 104784.	4.0	6
46	Low leakage current of CdSe quantum dots/Si composite structure and its performance for photodiode and solar cell. Ceramics International, 2016, 42, 14949-14955.	4.8	5
47	The effect of molar ratio on the photo-generated charge activity of ZnO–CdO composites. European Physical Journal Plus, 2020, 135, 1.	2.6	5
48	GaAs heterojunction devices with MDMO-PPV thin films. Vacuum, 2014, 106, 33-38.	3.5	4
49	The photovoltaic application and optics of ZnO–CdO and ZnO–NiO nanocomposite binary system. , 2022, 165, 207190.		4
50	Temperature-dependent model for hole transport mechanism in a poly(1.8-diaminocarbazole)/Si structure. Philosophical Magazine, 2016, 96, 2600-2614.	1.6	3
51	Low-Temperature Electrical Characteristics of Si-Based Device with New Tetrakis NiPc-SNS Active Layer. Journal of Electronic Materials, 2016, 45, 411-417.	2.2	3
52	n-GaAs diode with photoresponsivity based on 3-aminorhodanine thin films. Applied Optics, 2018, 57, 6788.	1.8	3
53	Improvement of Efficiency in CdS Quantum Dots Sensitized Solar Cells. Acta Physica Polonica A, 2013, 124, 750-754.	0.5	2
54	Thermally activated conductivity of Si hybrid structure based on ZnPc thin film. Applied Physics A: Materials Science and Processing, 2016, 122, 1.	2.3	2

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55	Surface coating of ZnO nanoparticles onto 6H-SiC(0001): Temperature-dependent rectifying behavior. Physica E: Low-Dimensional Systems and Nanostructures, 2016, 78, 85-91.	2.7	1
56	Investigating the coumarin capability in chalcogenide 20TI2Se–80Pr2Se3 system based photovoltaics. Spectrochimica Acta - Part A: Molecular and Biomolecular Spectroscopy, 2018, 202, 123-130.	3.9	1
57	Effects of Different TiO <sub>2</sub> Solution Compositions on Efficiency of Quantum Dot Solar Cell (QDSC) by Sol–Gel Method. Journal of Nanoelectronics and Optoelectronics, 2014, 9, 392-396.	0.5	0
58	EFFECT OF DOPING THIOUREA IN CdO THIN FILMS FOR ELECTRONIC APPLICATIONS. Surface Review and Letters, 2022, 29, .	1.1	0